BYW100-200

HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODE

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	1.5 A
V_{RRM}	200 V
Tj (max)	150 °C
V_F (max)	0.85 V

DO-15
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FEATURES AND BENEFITS

- Very low conduction losses
- Negligible switching losses
- Low forward and reverse recovery times
- The specifications and curves enable the determination of trr and I_{RM} at 100°C under users conditions.

DESCRIPTION

Low voltage drop and rectifier suited for switching mode base drive and transistor circuits.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		200	V
I_{FRM}	Repetitive peak forward current *	tp = 5µs F = 1KHz	80	A
$I_{F(AV)}$	Average forward current*	Ta = 95°C δ = 0.5	1.5	A
I_{FSM}	Surge non repetitive forward current	tp=10 ms Sinusoidal	50	A
T_{stg}	Storage temperature range		-65 +150	°C
Tj	Maximum operating junction temperature		+ 150	°C
T_L	Maximum lead temperature for soldering during 10s at 4mm from case		230	°C

* On infinitive heatsink with 10mm lead length

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th\ (j-a)}$	Junction to ambient*	45	°C/W

* On infinite heatsink with 10mm lead length.